

- (33) ("45471387" "5081559" "518[■])
- (3643) capacitor with ((sidewall spacer) or sp)
- (3624) ((capacitor with ((sidewall spacer) or sp))
- ((1128) ((capacitor with ((sidewall spacer) or sp))
- ((264) (((capacitor with ((sidewall spacer) or sp))
- ((C) (((capacitor with ((sidewall spacer) or sp))
- ((47) (((capacitor with ((sidewall spacer) or sp))
- ((111) (((((capacitor with ((sidewall spacer) or sp))
- ((2029) ((capacitor with ((sidewall spacer) or sp))
- ((595) ((capacitor with ((sidewall spacer) or sp))
- ((271) ((capacitor with ((sidewall spacer) or sp))
- ((99) ((capacitor with ((sidewall spacer) or sp))
- ((91) (((capacitor with ((sidewall spacer) or sp))
- ((79) (((((capacitor with ((sidewall spacer) or sp))
- ((40) (((((capacitor with ((sidewall spacer) or sp))
- ((111) (((((capacitor with ((sidewall spacer) or sp))
- ((111) (((((capacitor with ((sidewall spacer) or sp))
- ((3643) (capacitor with ((sidewall spacer) or sp))

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P Books

P highlight all terms in body

(((((capacitor with ((sidewall spacer) or sp))) not ((metal adj insulator adj metal) or (metal-insulator-metal) or ("MIN") and ((capacitor and ((lower adj electrode) or (bottom adj electrode) and (sidewall adj spacer)))) and channel) and ((titanium adj nitride) or ("TiN")) and ("Ti,sub.2 O,sub.5" or (tantalum adj pentoxide))) and (plasma)) and (ammonia)

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Retrieval

Document ID Issue Date Patented Title Current OR Current XR Retrieval

Inventor S C 3 4

1 F F F US 20021107 25 Mixed metal nitride and 257/205 Vaartstra, Brian P F F F F

boride barrier layers A. et al.

2 F F F US 20020627 75 Reduction of damage in 257/296 Zheng, Lingyu A. P F F F F

semiconductor container et al.

3 F F F F US 6538274 29930325 19 Reduction of damage in 257/296 Zheng, Lingyu A. P F F F F

semiconductor container A. et al.

4 F F F F US 6445028 20020993 23 Mixed metal nitride and 257/295 Vaartstra, Brian P F F F F

B1 boride barrier layers A. et al.

5 F F F F US 6432835 20020813 59 Process for fabricating 438/720 Yunogami, Takashi P F F F F

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6 F F F F US 6399339 20020604 26 Method for 438/3 438/240,-- Yunamoto, Tomio P F F F F

manufacturing 438/253

7 F F F F US 6218693 20010417 12 Dynamic random access Lu, Chih-Yuan P F F F F

memory (DRAM) cell 257/300,--

257/301,

Chen, Yinan et al. P F F F F

8 F F F F US 6149179 20000301 13 Method of forming a 438/254 257/E21.01 Jeng, Erick S. et P F F F F

crown capacitor for a 2,

9 F F F F US 6136643 20001024 17 Method for fabricating 438/253 257/E21.01 Jeng, Erick S. et P F F F F

capacitor-over-bit-line 9,

10 F F F F US 6010931 20000104 13 Planarization technique 438/243 257/E21.64 Sun, Shih-Wei et P F F F F

for DRAM cell capacitor 8,

11 F F F F US 6003674 20001229 10 Double depth etch 438/200,-- Chen, Yinan et al. P F F F F

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